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INFORMATION DISCLOSURE STATEMENT BY APPLICANT <small>(Use as many sheets as necessary)</small>		Complete if Known <table border="1" style="width: 100%; border-collapse: collapse;"> <tr> <td style="width: 30%;">Application Number</td> <td colspan="4">09/256643</td> </tr> <tr> <td>Filing Date</td> <td colspan="4">February 23, 1999</td> </tr> <tr> <td>First Named Inventor</td> <td colspan="4">Forbes, Leonard</td> </tr> <tr> <td>Group Art Unit</td> <td colspan="4">2822</td> </tr> <tr> <td>Examiner Name</td> <td colspan="4">Trinh, Michael</td> </tr> </table>					Application Number	09/256643				Filing Date	February 23, 1999				First Named Inventor	Forbes, Leonard				Group Art Unit	2822				Examiner Name	Trinh, Michael			
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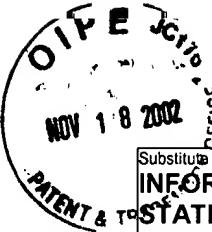
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